

Please replace the paragraph beginning on page 6, line 19, with the following rewritten paragraph:

A2
--The slurry containing about 2 wt% of HNO_3 and about 2 wt% of ceric ammonium nitrate has a polishing rate of about 1000 Å/min under a polishing pressure of 4 psi, the disclosed slurry obtains a polishing rate over 1000 Å/min even under a polishing pressure of 1 psi, by slightly increasing a content of HNO_3 and ceric ammonium nitrate.--

Please replace the paragraph beginning on page 11, line 19, with the following rewritten paragraph:

A3
--A table revolution number and a wafer revolution number were respectively set up to be 20 rpm and 80 rpm, by using a rotary type system. Here, the CMP process was performed on the ruthenium film under a polishing pressure of 1 psi by using the slurry prepared in Example 1 (polishing rate is about 600 Å/min).--

Please replace the paragraph beginning on page 12, line 4, with the following rewritten paragraph:

A4
--The procedure of Example 6 was repeated but using the slurry prepared in Example 2, instead of using the slurry prepared in Example 1 (polishing rate is about 1200 Å/min).--

Please replace the paragraph beginning on page 12, line 8, with the following rewritten paragraph:

A5
--The procedure of Example 6 was repeated but using the slurry prepared in Example 3, instead of using the slurry prepared in Example 1 (polishing rate is about 1400 Å/min).--

Please replace the paragraph beginning on page 12, line 10, with the following rewritten paragraph:

A6
--The procedure of Example 6 was repeated but using the slurry prepared in Example 4, instead of using the slurry prepared in Example 1 (polishing rate is about 1050 Å/min).--